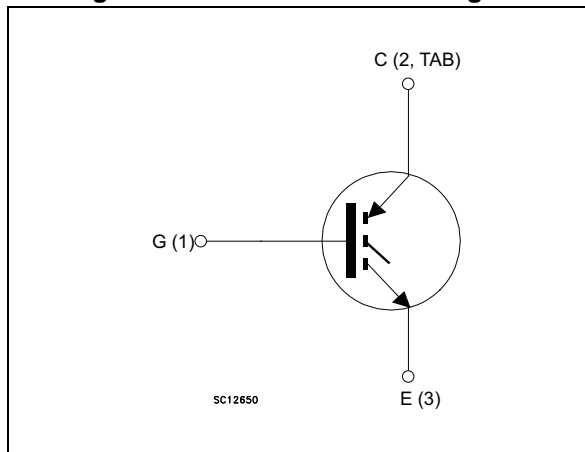


Figure 1. Internal schematic diagram



Features

- Maximum junction temperature: $T_J = 175\text{ °C}$
- Tail-less switching off
- $V_{CE(sat)} = 1.8\text{ V (typ.) @ } I_C = 40\text{ A}$
- Tight parameters distribution
- Safe paralleling
- Low thermal resistance

Applications

- Photovoltaic inverters
- Uninterruptible power supply
- Welding
- Power factor correction
- Very high frequency converters

Description

This device is an IGBT developed using an advanced proprietary trench gate field stop structure. The device is part of the V series of IGBTs, which represent an optimum compromise between conduction and switching losses to maximize the efficiency of very high frequency converters. Furthermore, a positive $V_{CE(sat)}$ temperature coefficient and very tight parameter distribution result in safer paralleling operation.

Table 1. Device summary

Order code	Marking	Package	Packaging
STGB40V60F	GB40V60F	D ² PAK	Tape and reel
STGFW40V60F	GFW40V60F	TO-3PF	Tube
STGP40V60F	GP40V60F	TO-220	Tube
STGW40V60F	GW40V60F	TO-247	Tube

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1 Electrical ratings

Table 2. Absolute maximum ratings

Symbol	Parameter	Value		Unit
		D ² PAK TO-247 TO-3P	TO-3PF	
V _{CES}	Collector-emitter voltage (V _{GE} = 0)	600		V
I _C	Continuous collector current at T _C = 25 °C	80		A
I _C	Continuous collector current at T _C = 100 °C	40		A
I _{CP} ⁽¹⁾	Pulsed collector current	160		A
V _{GE}	Gate-emitter voltage	±20		V
P _{TOT}	Total dissipation at T _C = 25 °C	283	62.5	W
V _{ISO}	Insulation withstand voltage (RMS) from all three leads to external heat sink (t = 1 s; T _c = 25 °C)		3.5	kV
T _{STG}	Storage temperature range	- 55 to 150		°C
T _J	Operating junction temperature	- 55 to 175		°C

1. Pulse width limited by maximum junction temperature

Table 3. Thermal data

Symbol	Parameter	Value		Unit
		D ² PAK TO-247 TO-3P	TO-3PF	
R _{thJC}	Thermal resistance junction-case	0.53	2.4	°C/W
R _{thJA}	Thermal resistance junction-ambient	50		°C/W

2 Electrical characteristics

$T_J = 25\text{ °C}$ unless otherwise specified.

Table 4. Static characteristics

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)CES}$	Collector-emitter breakdown voltage ($V_{GE} = 0$)	$I_C = 2\text{ mA}$	600			V
$V_{CE(sat)}$	Collector-emitter saturation voltage	$V_{GE} = 15\text{ V}, I_C = 40\text{ A}$		1.8	2.3	V
		$V_{GE} = 15\text{ V}, I_C = 40\text{ A}$ $T_J = 125\text{ °C}$		2.15		
		$V_{GE} = 15\text{ V}, I_C = 40\text{ A}$ $T_J = 175\text{ °C}$		2.35		
$V_{GE(th)}$	Gate threshold voltage	$V_{CE} = V_{GE}, I_C = 1\text{ mA}$	5	6	7	V
I_{CES}	Collector cut-off current ($V_{GE} = 0$)	$V_{CE} = 600\text{ V}$			25	μA
I_{GES}	Gate-emitter leakage current ($V_{CE} = 0$)	$V_{GE} = \pm 20\text{ V}$			250	nA

Table 5. Dynamic characteristics

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
C_{ies}	Input capacitance	$V_{CE} = 25\text{ V}, f = 1\text{ MHz},$ $V_{GE} = 0$	-	5400	-	pF
C_{oes}	Output capacitance		-	220	-	pF
C_{res}	Reverse transfer capacitance		-	180	-	pF
Q_g	Total gate charge	$V_{CC} = 480\text{ V}, I_C = 40\text{ A},$ $V_{GE} = 15\text{ V},$ see Figure 28	-	226	-	nC
Q_{ge}	Gate-emitter charge		-	38	-	nC
Q_{gc}	Gate-collector charge		-	95	-	nC

Table 6. Switching characteristics (inductive load)

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}^{(1)}$	Turn-on delay time	$V_{CE} = 400\text{ V}$, $I_C = 40\text{ A}$, $R_G = 10\ \Omega$, $V_{GE} = 15\text{ V}$, see Figure 27	-	52	-	ns
$t_r^{(1)}$	Current rise time		-	17	-	ns
$(di/dt)_{on}^{(1)}$	Turn-on current slope		-	1850	-	A/ μ s
$t_{d(off)}$	Turn-off delay time		-	208	-	ns
t_f	Current fall time		-	20	-	ns
$E_{on}^{(1)}$	Turn-on switching losses		-	456	-	μ J
$E_{off}^{(2)}$	Turn-off switching losses		-	411	-	μ J
E_{ts}	Total switching losses		-	867	-	μ J
$t_{d(on)}^{(1)}$	Turn-on delay time	$V_{CE} = 400\text{ V}$, $I_C = 40\text{ A}$, $R_G = 10\ \Omega$, $V_{GE} = 15\text{ V}$, $T_J = 175\text{ }^\circ\text{C}$, see Figure 27	-	52	-	ns
$t_r^{(1)}$	Current rise time		-	21	-	ns
$(di/dt)_{on}^{(1)}$	Turn-on current slope		-	1538	-	A/ μ s
$t_{d(off)}$	Turn-off delay time		-	220	-	ns
t_f	Current fall time		-	21	-	ns
$E_{on}^{(1)}$	Turn-on switching losses		-	1330	-	μ J
$E_{off}^{(2)}$	Turn-off switching losses		-	560	-	μ J
E_{ts}	Total switching losses		-	1890	-	μ J

1. Energy losses include reverse recovery of the external diode. The diode is the same of the co-packed STGW40V60DF.
2. Turn-off losses include also the tail of the collector current.

2.1 Electrical characteristics (curves)

Figure 2. Power dissipation vs. case temperature for D²PAK, TO-247 and TO-3P

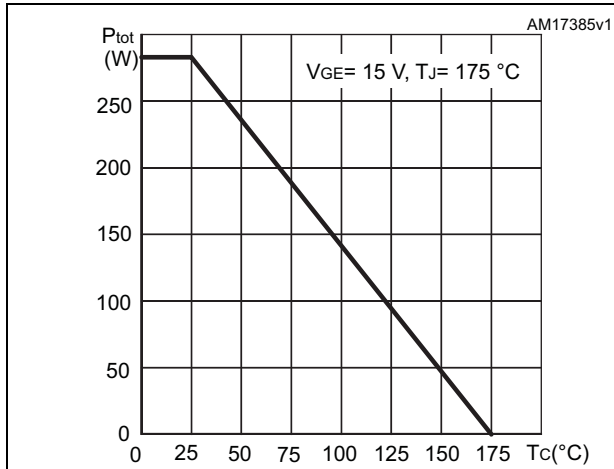


Figure 3. Collector current vs. case temperature for D²PAK, TO-247 and TO-3P

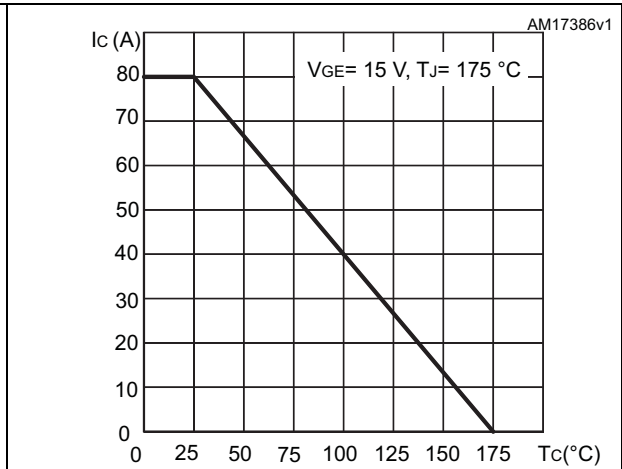


Figure 4. Power dissipation vs. case temperature for TO-3PF

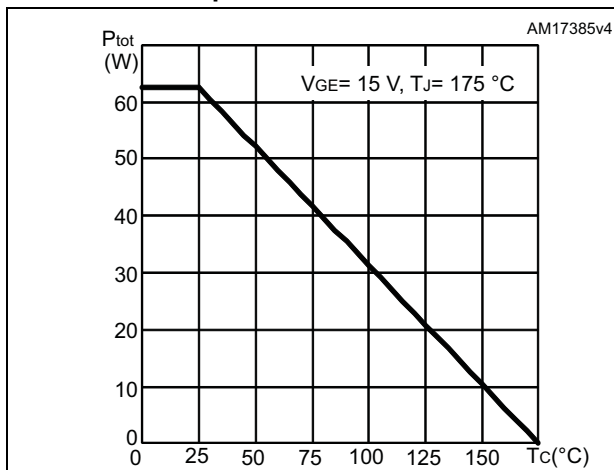


Figure 5. Collector current vs. case temperature for TO-3PF

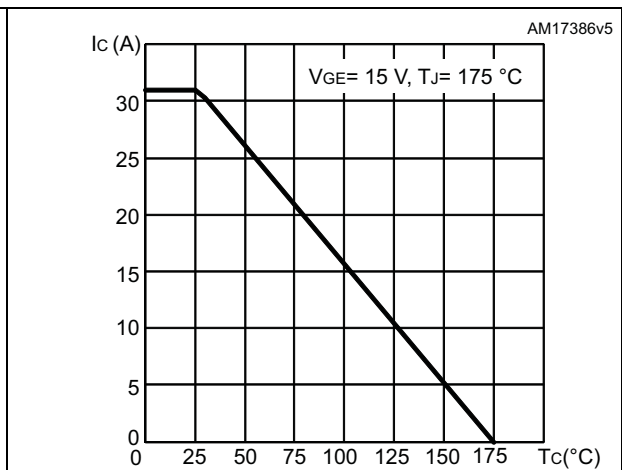


Figure 6. Output characteristics (T_J=25°C)

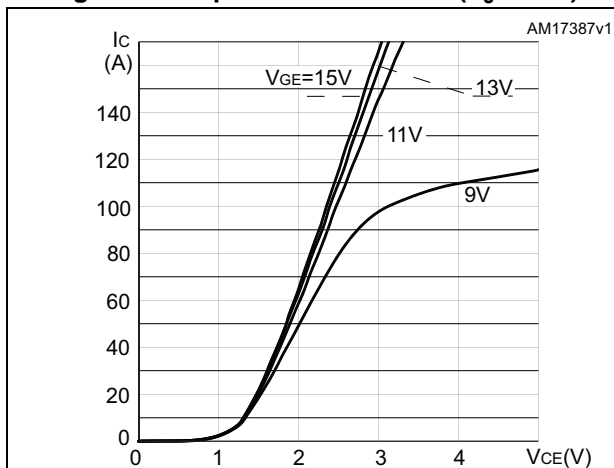


Figure 7. Output characteristics (T_J=175°C)

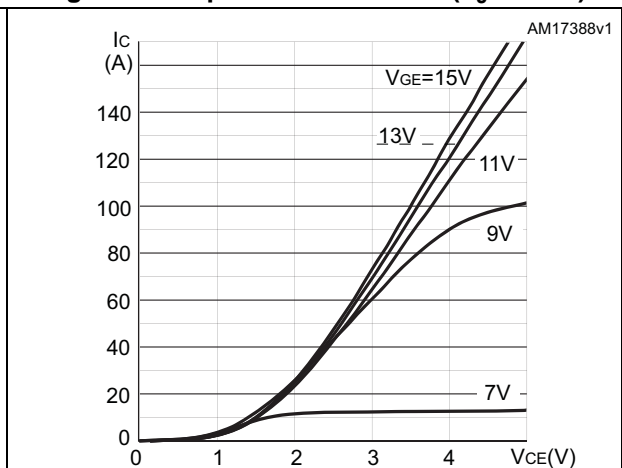


Figure 8. $V_{CE(sat)}$ vs. junction temperature

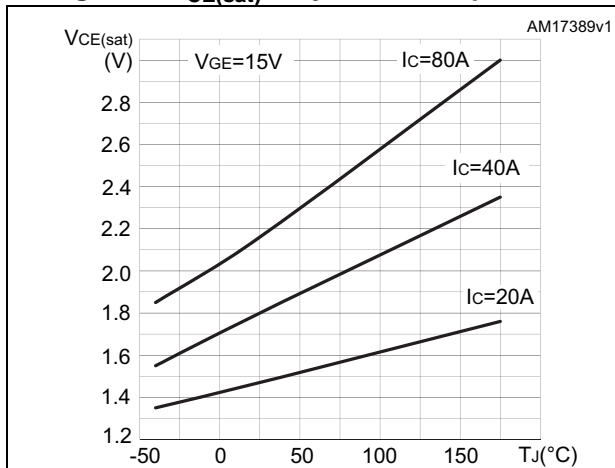


Figure 9. $V_{CE(sat)}$ vs. collector current

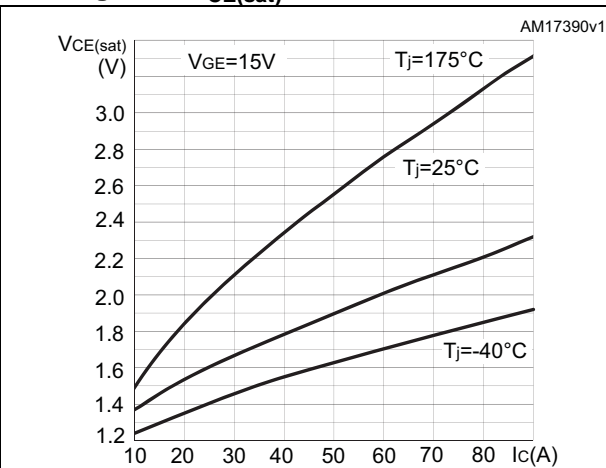


Figure 10. Collector current vs. switching frequency for D²PAK, TO-247 and TO-3P

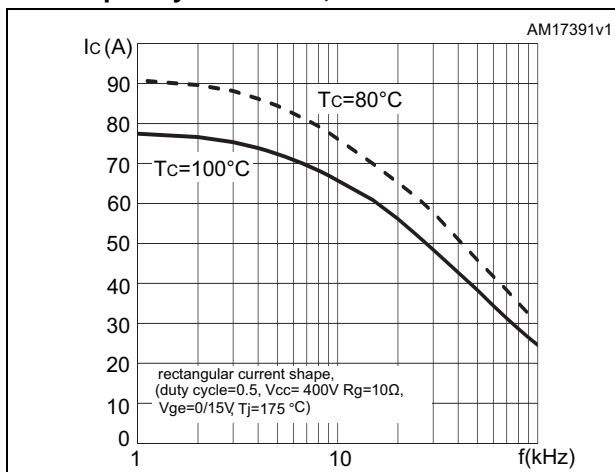


Figure 11. Collector current vs. switching frequency for TO-3PF

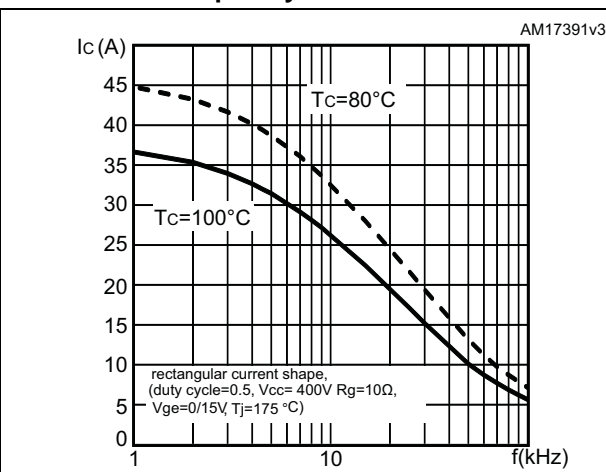


Figure 12. Forward bias safe operating area for D²PAK, TO-247 and TO-3P

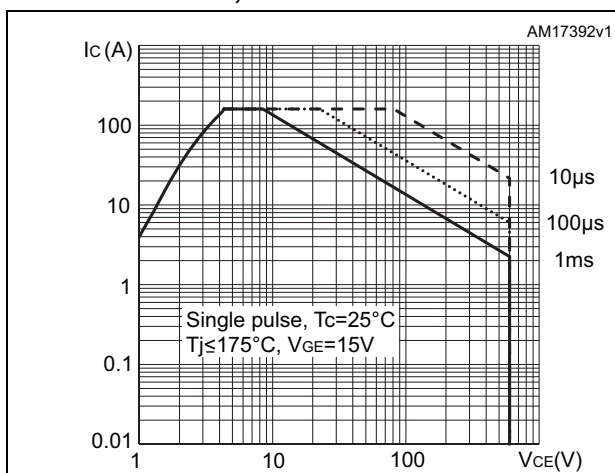


Figure 13. Forward bias safe operating area for TO-3PF

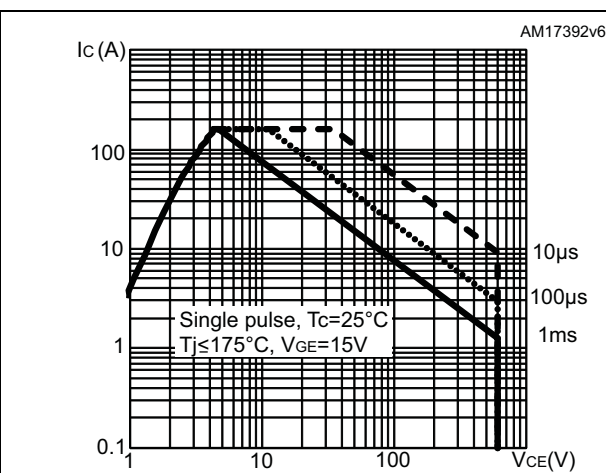


Figure 14. Transfer characteristics

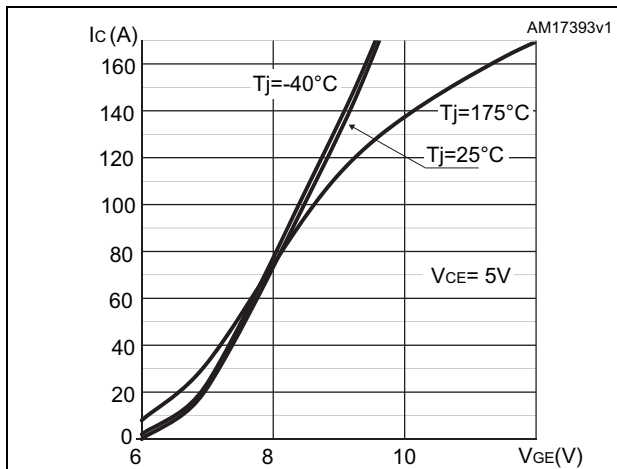


Figure 15. Normalized $V_{GE(th)}$ vs junction temperature

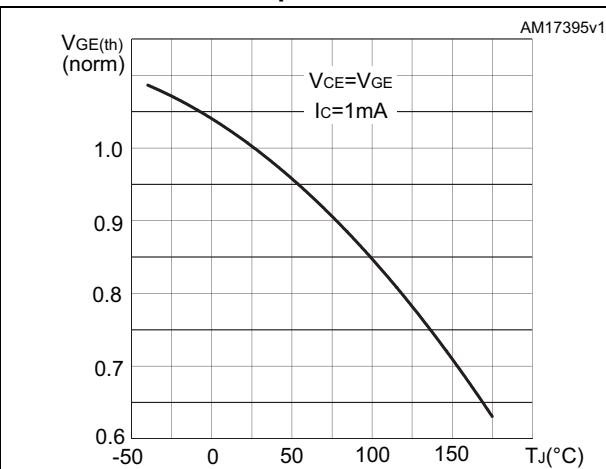


Figure 16. Normalized $V_{(BR)CES}$ vs. junction temperature

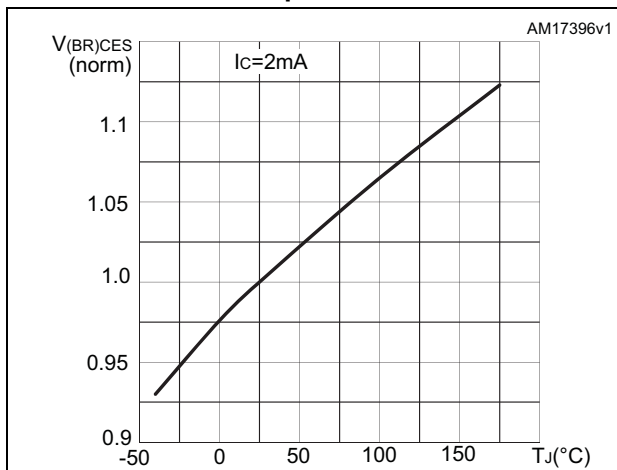


Figure 17. Capacitance variations

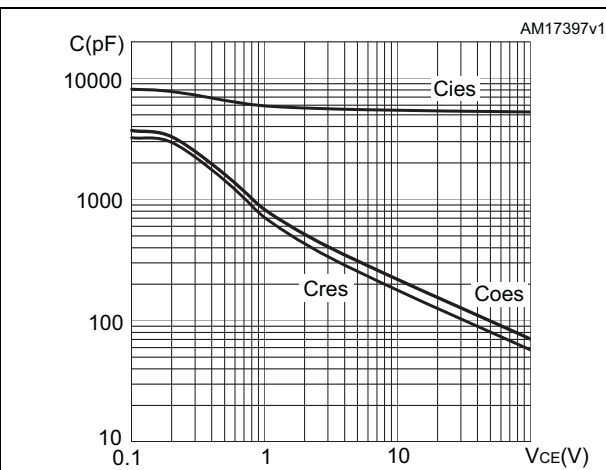


Figure 18. Gate charge vs. gate-emitter voltage

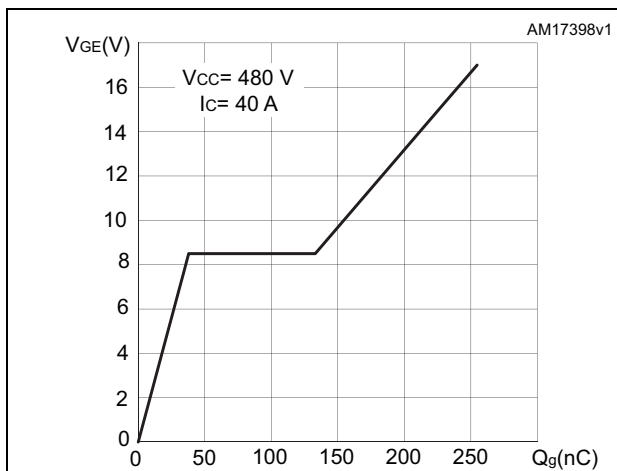


Figure 19. Switching losses vs. collector current

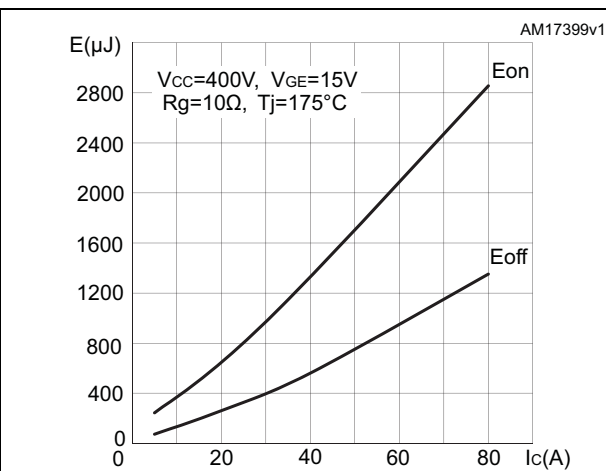


Figure 20. Switching losses vs. gate resistance

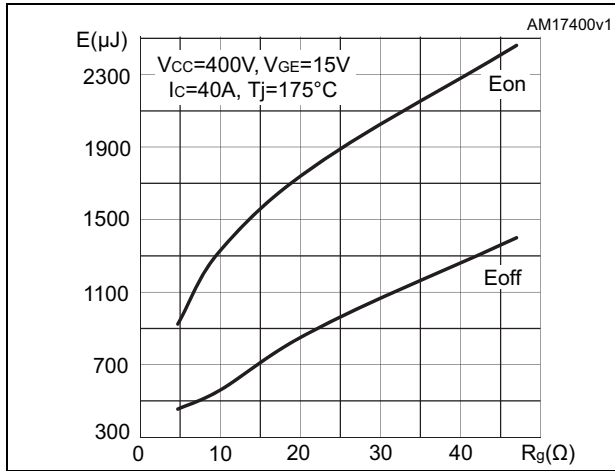


Figure 21. Switching losses vs. junction temperature

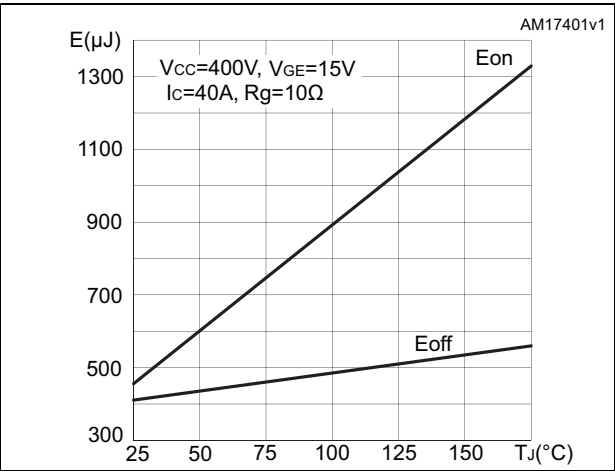


Figure 22. Switching losses vs. collector emitter voltage

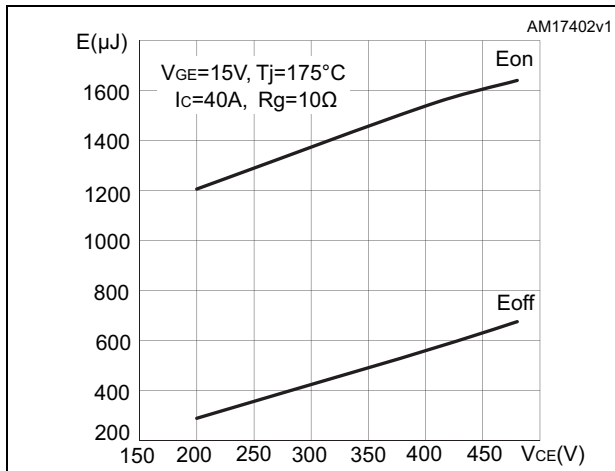


Figure 23. Switching times vs. collector current

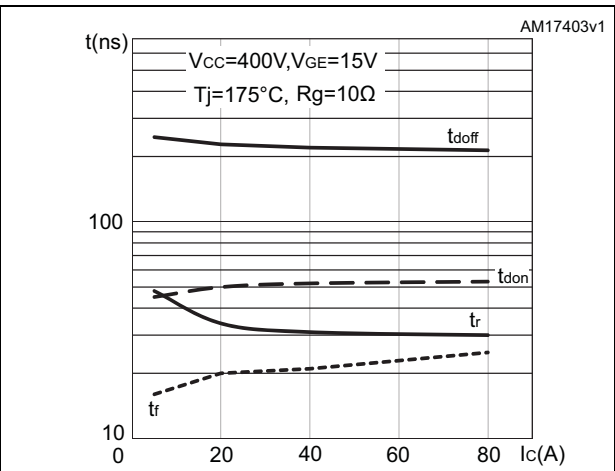


Figure 24. Switching times vs. gate resistance

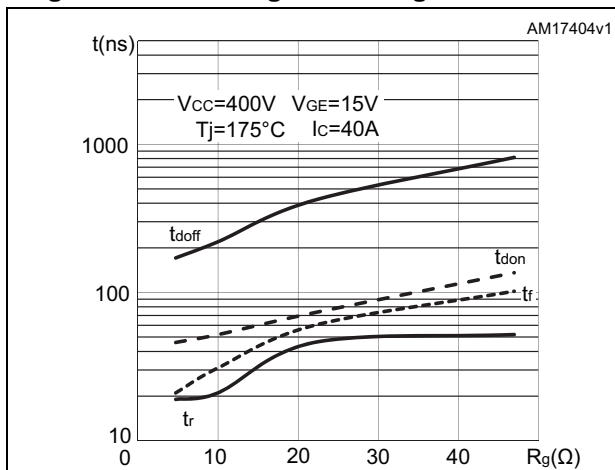


Figure 25. Thermal data for D²PAK, TO-247 and TO-3P

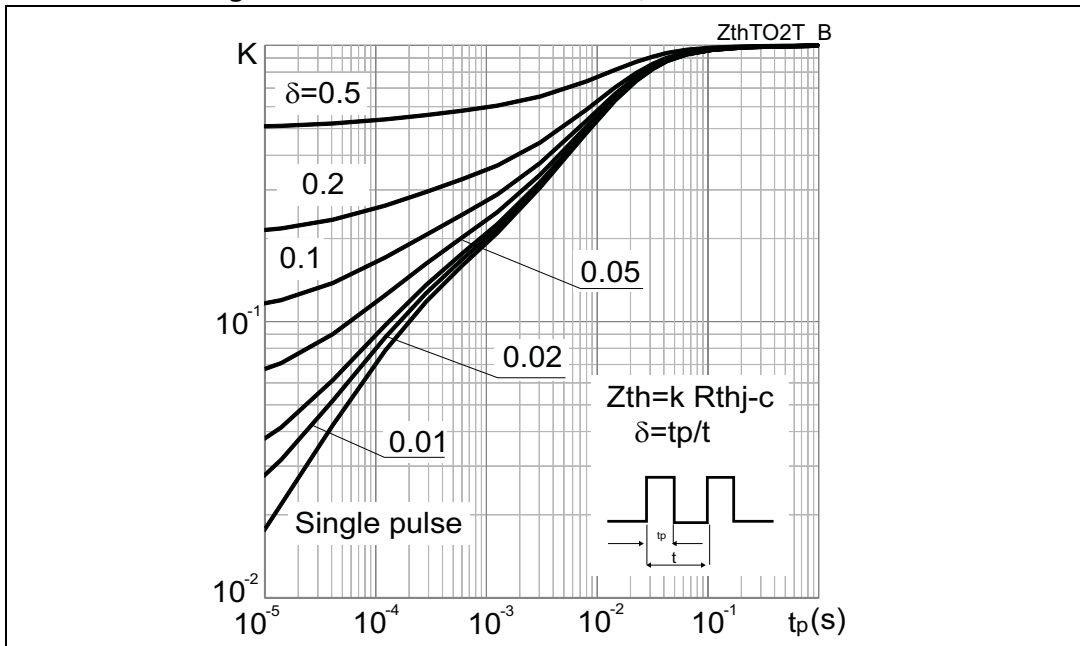
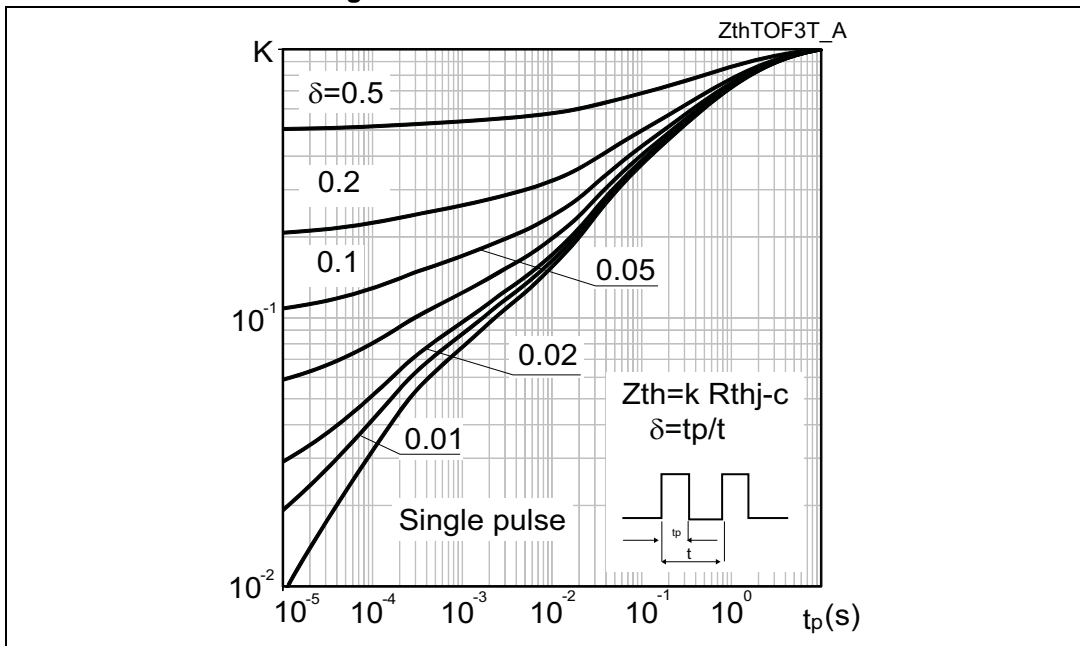


Figure 26. Thermal data for TO-3PF



3 Test circuits

Figure 27. Test circuit for inductive load switching



Figure 28. Gate charge test circuit

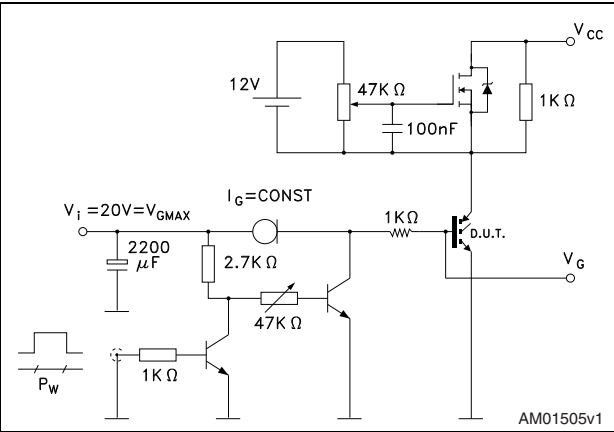


Figure 29. Switching waveform



4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK[®] packages, depending on their level of environmental compliance. ECOPACK[®] specifications, grade definitions and product status are available at: www.st.com. ECOPACK is an ST trademark.

4.1 D²PAK, STGB40V60F

Figure 30. D²PAK (TO-263) drawing

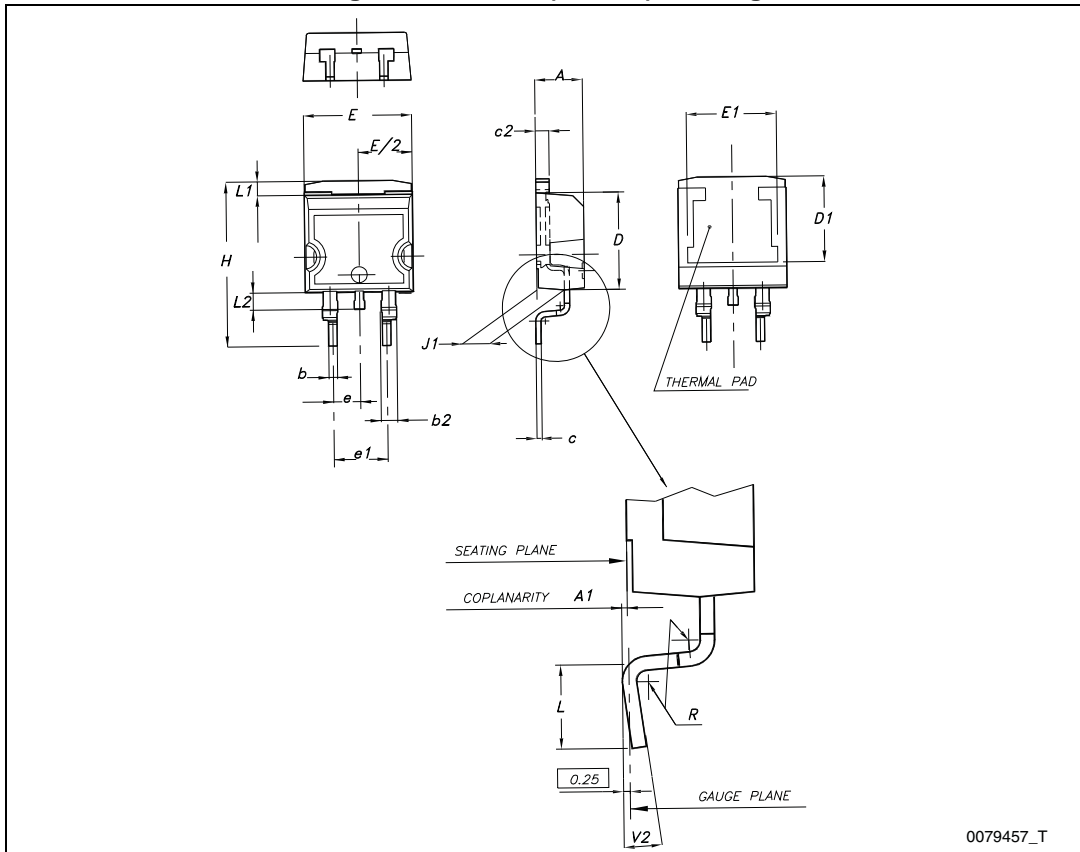
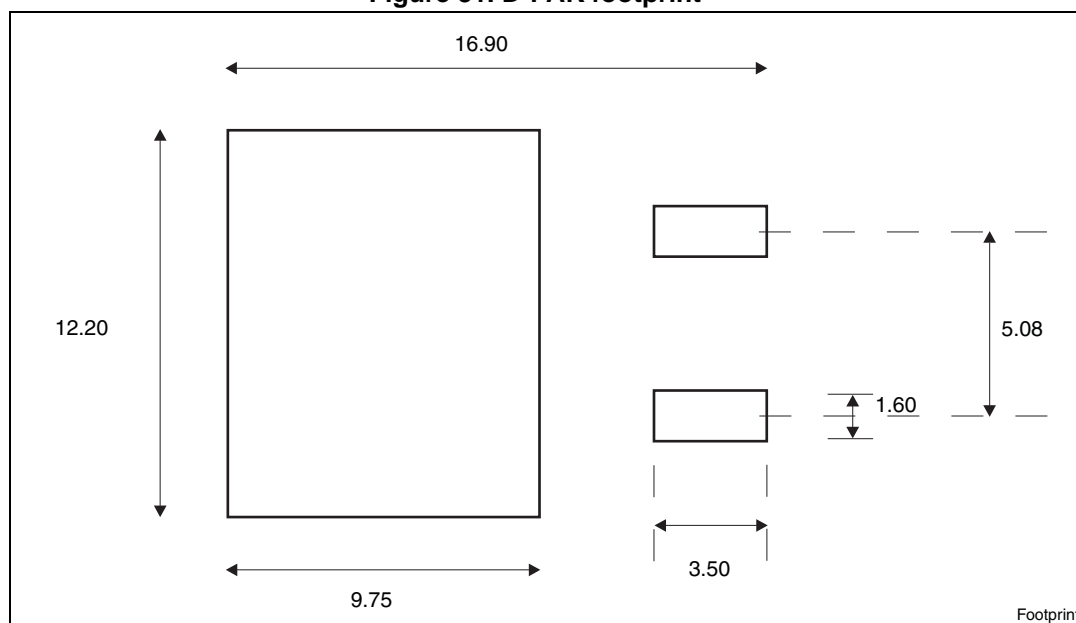


Table 7. D²PAK (TO-263) mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	4.40		4.60
A1	0.03		0.23
b	0.70		0.93
b2	1.14		1.70
c	0.45		0.60
c2	1.23		1.36
D	8.95		9.35
D1	7.50		
E	10		10.40
E1	8.50		
e		2.54	
e1	4.88		5.28
H	15		15.85
J1	2.49		2.69
L	2.29		2.79
L1	1.27		1.40
L2	1.30		1.75
R		0.4	
V2	0°		8°

Figure 31. D²PAK footprint^(a)



a. All dimension are in millimeters

4.2 TO-3PF, STGFW40V60F

Figure 32. TO-3PF drawing

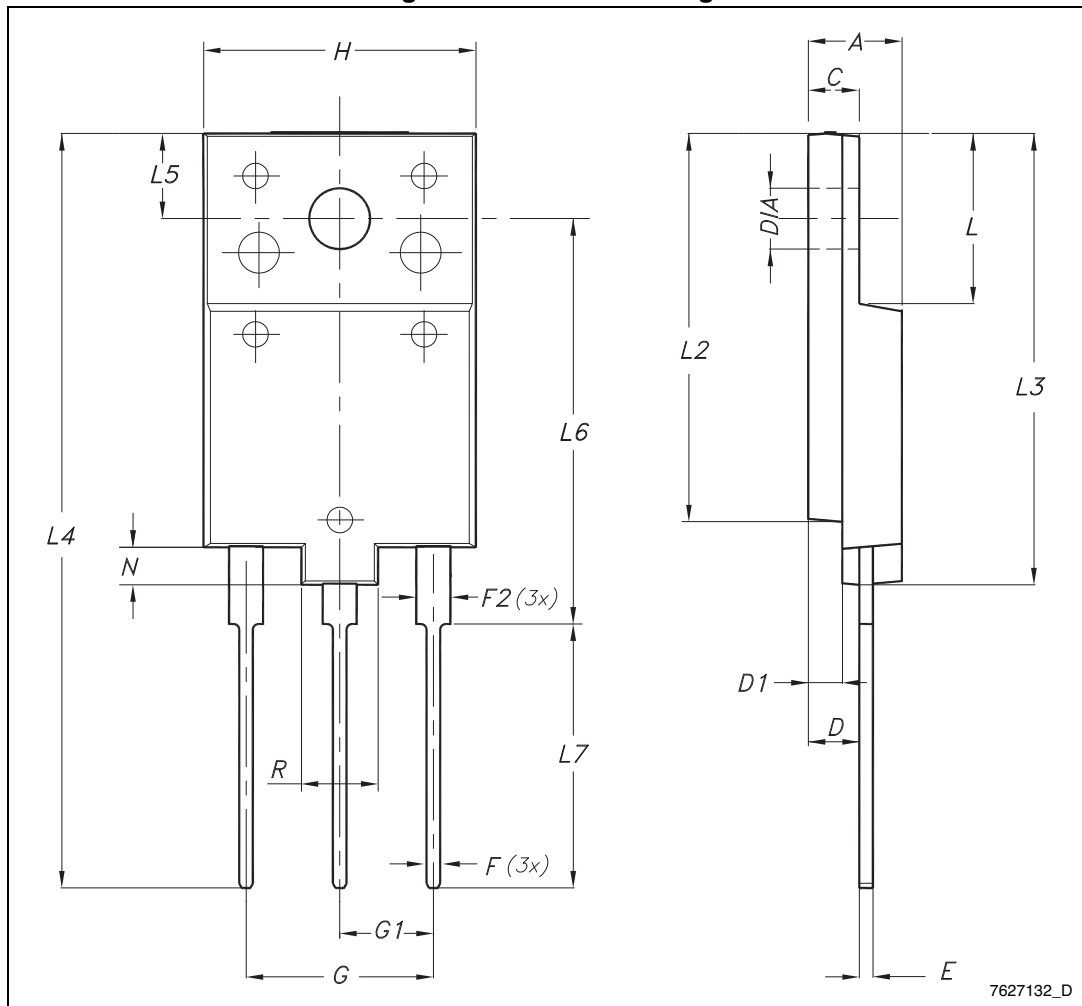


Table 8. TO-3PF mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	5.30		5.70
C	2.80		3.20
D	3.10		3.50
D1	1.80		2.20
E	0.80		1.10
F	0.65		0.95
F2	1.80		2.20
G	10.30		11.50
G1		5.45	
H	15.30		15.70
L	9.80	10	10.20
L2	22.80		23.20
L3	26.30		26.70
L4	43.20		44.40
L5	4.30		4.70
L6	24.30		24.70
L7	14.60		15
N	1.80		2.20
R	3.80		4.20
Dia	3.40		3.80

4.3 TO-220, STGP40V60F

Figure 33. TO-220 type A drawing

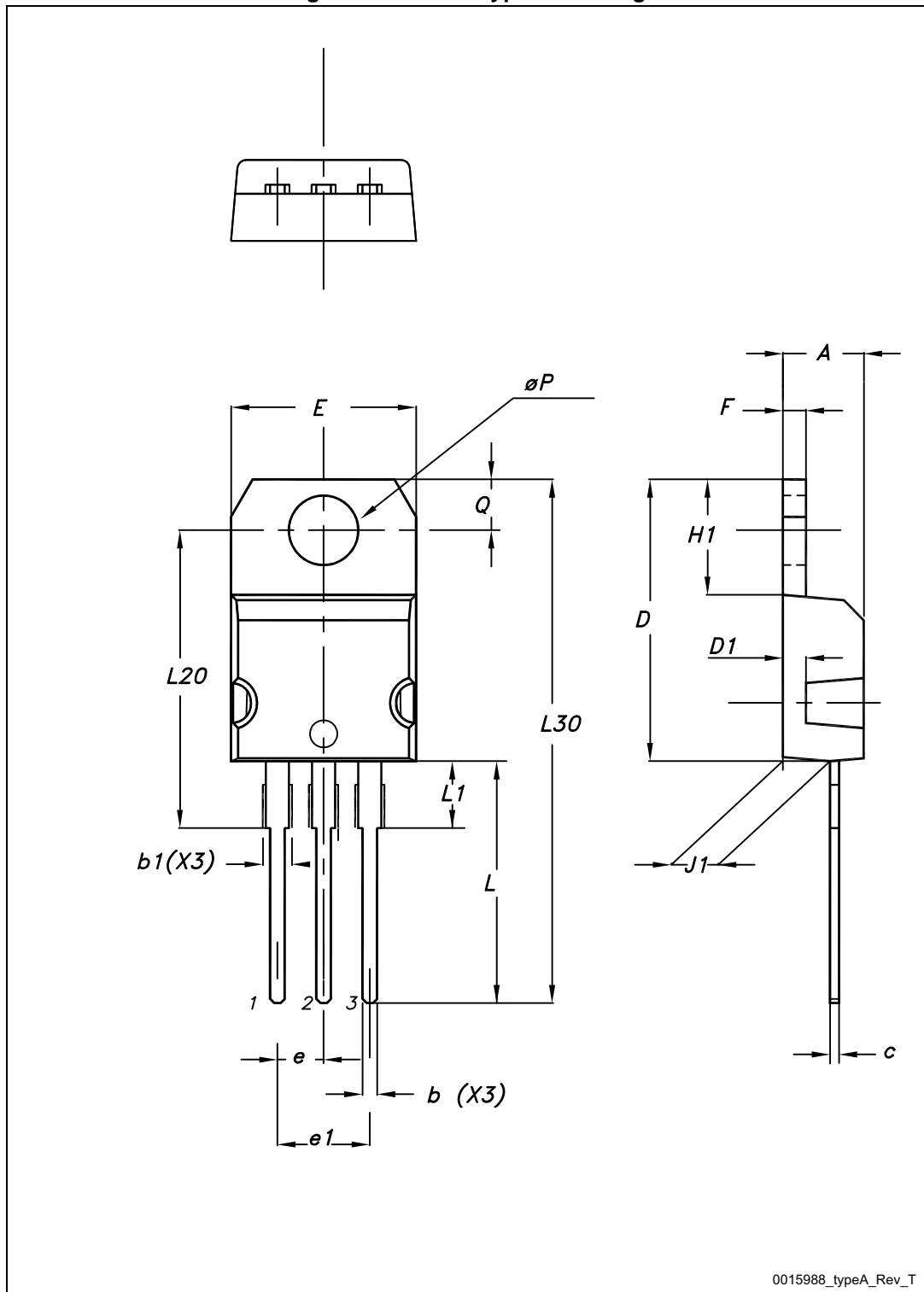


Table 9. TO-220 type A mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	4.40		4.60
b	0.61		0.88
b1	1.14		1.70
c	0.48		0.70
D	15.25		15.75
D1		1.27	
E	10		10.40
e	2.40		2.70
e1	4.95		5.15
F	1.23		1.32
H1	6.20		6.60
J1	2.40		2.72
L	13		14
L1	3.50		3.93
L20		16.40	
L30		28.90	
ØP	3.75		3.85
Q	2.65		2.95

4.4 TO-247, STGW40V60F

Figure 34. TO-247 drawing

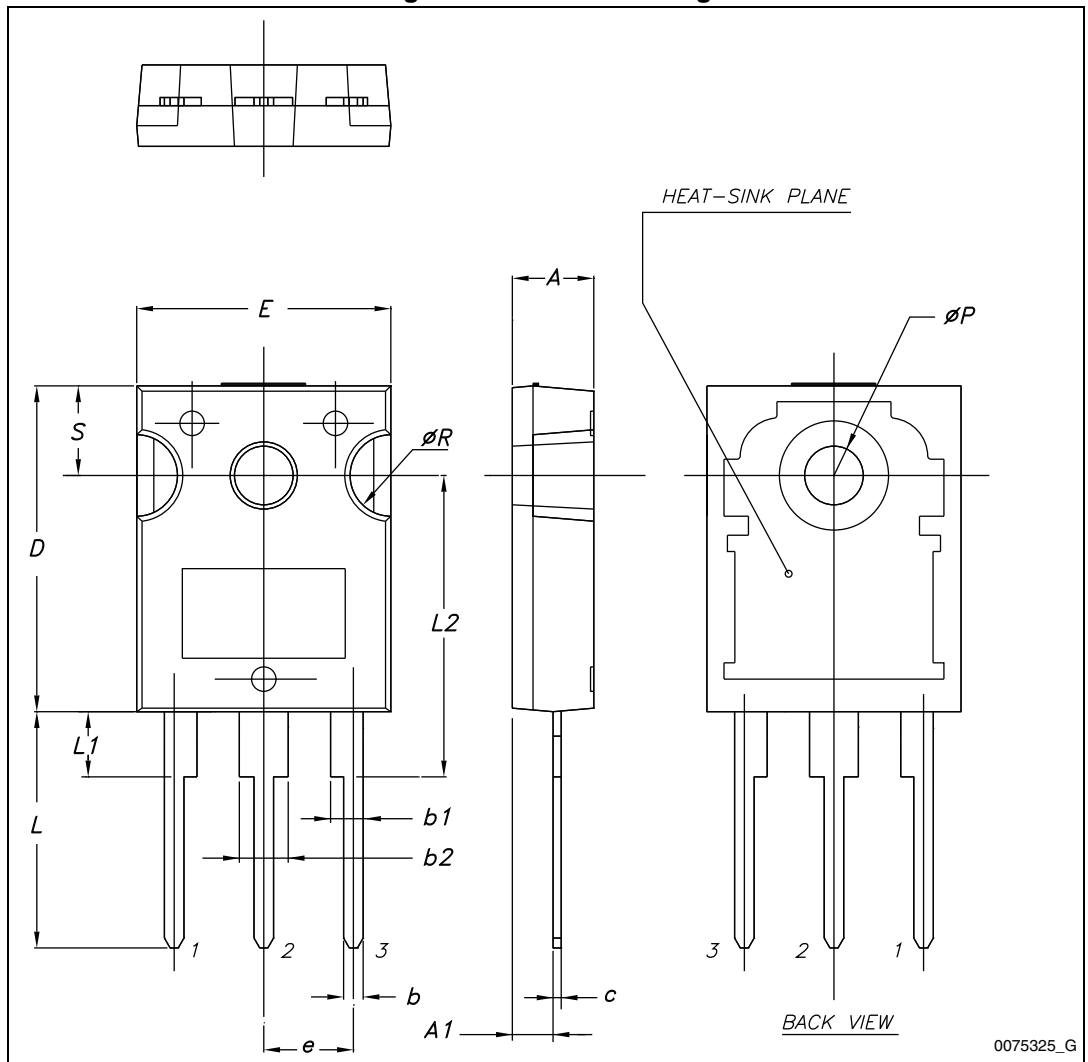


Table 10. TO-247 mechanical data

Dim.	mm.		
	Min.	Typ.	Max.
A	4.85		5.15
A1	2.20		2.60
b	1.0		1.40
b1	2.0		2.40
b2	3.0		3.40
c	0.40		0.80
D	19.85		20.15
E	15.45		15.75
e	5.30	5.45	5.60
L	14.20		14.80
L1	3.70		4.30
L2		18.50	
ØP	3.55		3.65
ØR	4.50		5.50
S	5.30	5.50	5.70

5 Packaging mechanical data

Figure 35. Tape

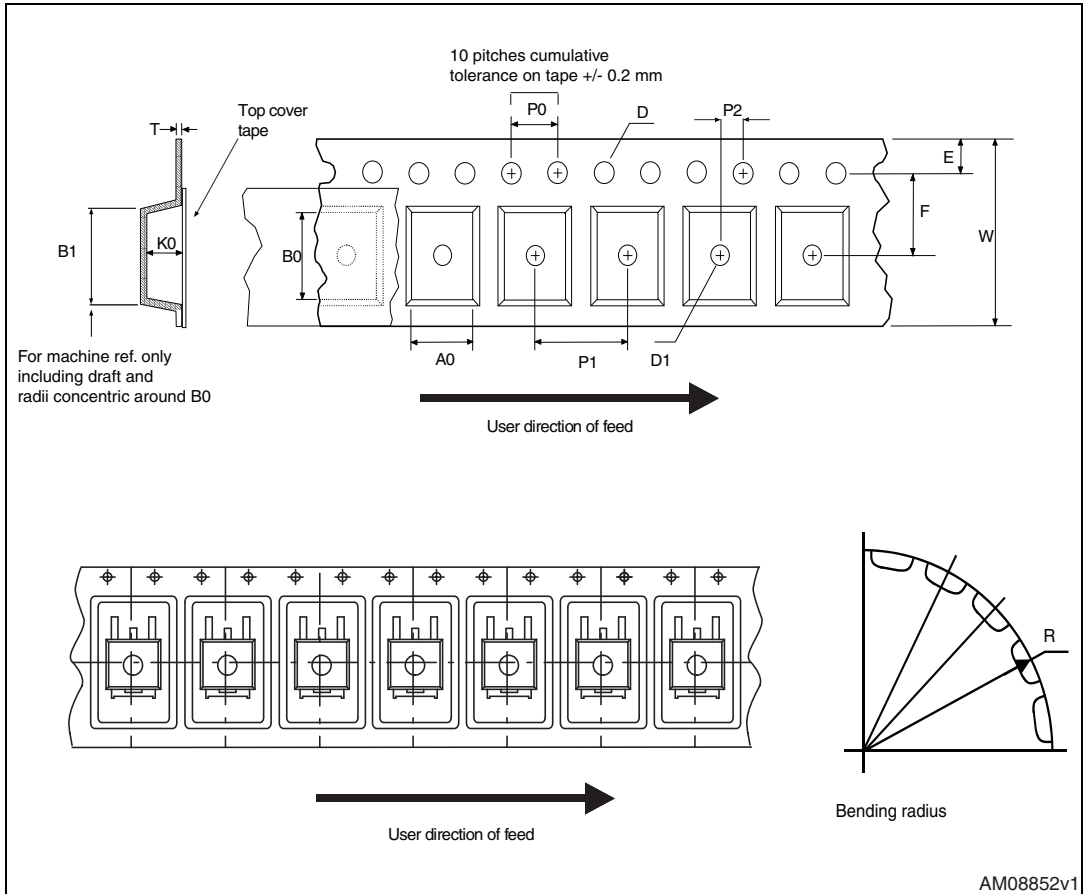


Figure 36. Reel

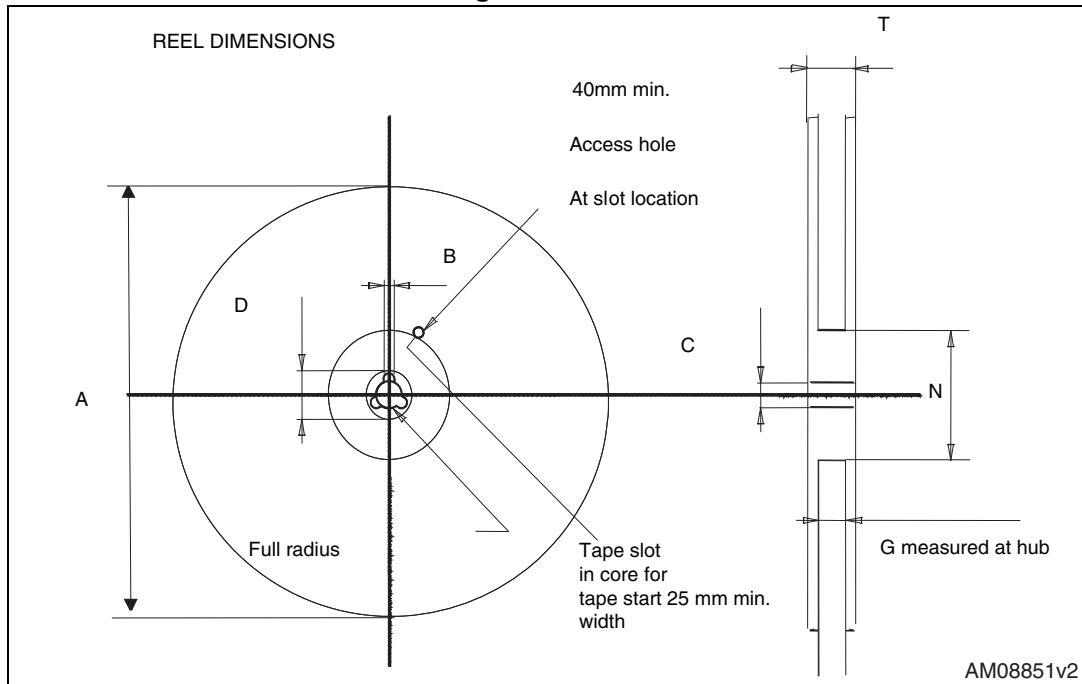


Table 11. D²PAK (TO-263) tape and reel mechanical data

Tape			Reel		
Dim.	mm		Dim.	mm	
	Min.	Max.		Min.	Max.
A0	10.5	10.7	A		330
B0	15.7	15.9	B	1.5	
D	1.5	1.6	C	12.8	13.2
D1	1.59	1.61	D	20.2	
E	1.65	1.85	G	24.4	26.4
F	11.4	11.6	N	100	
K0	4.8	5.0	T		30.4
P0	3.9	4.1			
P1	11.9	12.1		Base qty	1000
P2	1.9	2.1		Bulk qty	1000
R	50				
T	0.25	0.35			
W	23.7	24.3			

6 Revision history

Table 12. Document revision history

Date	Revision	Changes
04-Jun-2013	1	Initial release.
23-Apr-2014	2	Updated title, features and description in cover page. Added new device in TO-3PF. Updated Table 1: Device summary , Table 2: Absolute maximum ratings Table 3: Thermal data and Section 4: Package mechanical data . Added Figure 4: Power dissipation vs. case temperature for TO-3PF , Figure 5: Collector current vs. case temperature for TO-3PF , Figure 11: Collector current vs. switching frequency for TO-3PF and Figure 12: Forward bias safe operating area for D²PAK, TO-247 and TO-3P . Minor text changes.